



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Katsunori UENO

Serial No.: 10/646,586

Group Art Unit: 2811

Filed: August 22, 2003

Examiner:

For: SILICON CARBIDE n CHANNEL MOS SEMICONDUCTOR  
DEVICE AND METHOD FOR MANUFACTURING THE SAME

Certificate of Mailing

I hereby certify that this paper is being deposited with the  
United States Postal Service as first class mail in an envelope  
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Date: 11-19-03

By: [Signature]

Marc A. Rossi

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.56, the attention of the Patent and Trademark Office is hereby  
directed to the references listed on the attached Form PTO-1449. Copies of the references listed on  
Form PTO-1449 are attached.

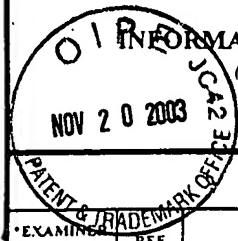
It is respectfully requested that the information be expressly considered during the  
prosecution of this application, that these references be made of record therein and appear among  
the "References Cited" on any patent to issue therefrom, and that an initialed copy of the PTO-1449  
be returned to the undersigned.

Respectfully submitted,

Date: 11-19-03

[Signature]  
Marc A. Rossi  
Registration No. 31,923

Attorney Docket No.: FUJI:141A

**INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

Docket Number (Optional)

FUJI:141A

Application Number

10/646,586

Applicant(s)

Katsunori UENO

Filing Date

August 22, 2003

Group Art Unit

2811

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 5,776,837	7/98	Palmour	438	767	
		US 5,506,421	4/96	Palmour	257	77	
		US 6,002,143	12/99	Terasawa	257	77	

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

		"Vital Issues for SiC Power Devices"; K. Hara; Materials Science Forum Vols. 264-268 (1998); pgs. 901-906; 1998 Trans Tech Publications, Switzerland
		"High Voltage Planar 6H-SiC Accufet"; P.M. Shenoy et al.; Materials Science Forum Vols. 264-268 (1998); pgs. 993-996; 1998 Trans Tech Publications, Switzerland

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.